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[File 351] **Derwent WPI** 1963-2008/UD=200804

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JP 2125654

WPI Acc no: 1990-190066/**199025**

XRXPX Acc No: N1990-147830

Semiconductor capacitor element - has polysilicon layer formed on spaced insulator layers within island on semiconductor substrate NoAbstract Dwg 1/3

Patent Assignee: NEC CORP (NIDE)

Inventor: OKIZAKI H

Patent Family (1 patents, 1 countries)

Patent Number	Kind	Date	Application Number	Kind	Date	Update	Type
JP 2125654	A	19900514	JP 1988279716	A	19881104	199025	B

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Class Codes

International Patent Classification

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H01L-0021/822	A	I	L	R	20060101
H01L-0027/04	A	I	F	R	20060101
H01L-0021/70	C	I	L	R	20060101
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SEMICONDUCTOR CAPACITANCE ELEMENT

Assignee: NEC CORP (NIDE)

Inventor: OKIZAKI HIROAKI

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